

**3LP02M**

## Ultrahigh-Speed Switching Applications

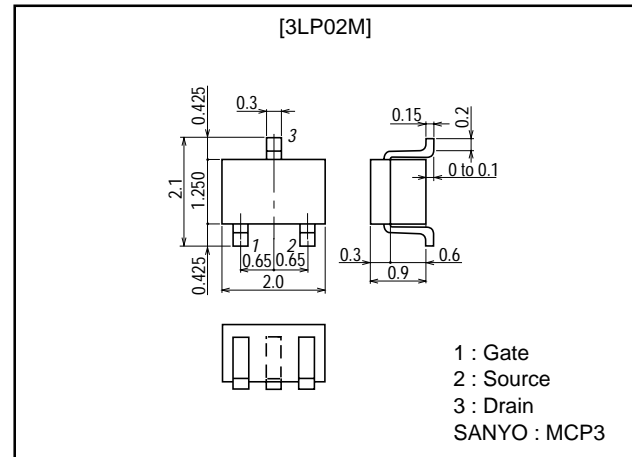
### Features

- Low ON resistance.
- Ultrahigh-speed switching.
- 2.5V drive.

### Package Dimensions

unit:mm

2158



### Specifications

#### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	$V_{DSS}$		-30	V
Gate-to-Source Voltage	$V_{GSS}$		±10	V
Drain Current (DC)	$I_D$		-0.2	A
Drain Current (pulse)	$I_{DP}$	$PW \leq 10 \mu s$ , duty cycle $\leq 1\%$	-0.8	A
Allowable Power Dissipation	$P_D$		0.15	W
Channel Temperature	$T_{ch}$		150	°C
Storage Temperature	$T_{stg}$		-55 to +150	°C

#### Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1mA$ , $V_{GS} = 0$	-30			V
Zero-Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -30V$ , $V_{GS} = 0$			-10	μA
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 8V$ , $V_{DS} = 0$			±10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10V$ , $I_D = -100 \mu A$	-0.4		-1.4	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS} = -10V$ , $I_D = -100mA$	0.21	0.3		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D = -100mA$ , $V_{GS} = -4V$		2.4	3.1	Ω
	$R_{DS(on)2}$	$I_D = -50mA$ , $V_{GS} = -2.5V$		3.5	4.9	Ω
	$R_{DS(on)3}$	$I_D = -10mA$ , $V_{GS} = -1.5V$		10	20	Ω

Marking : XD

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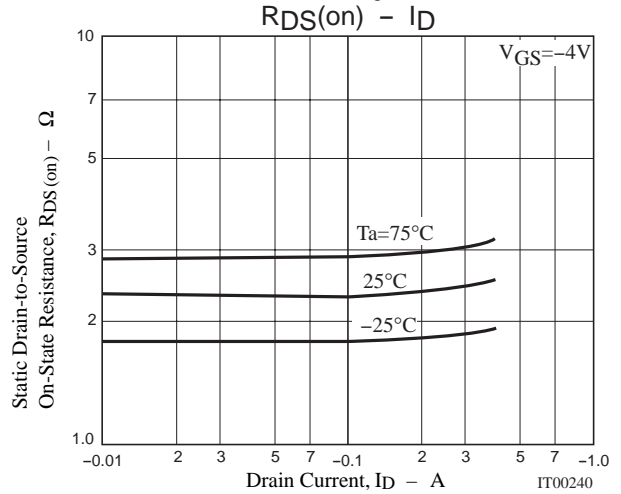
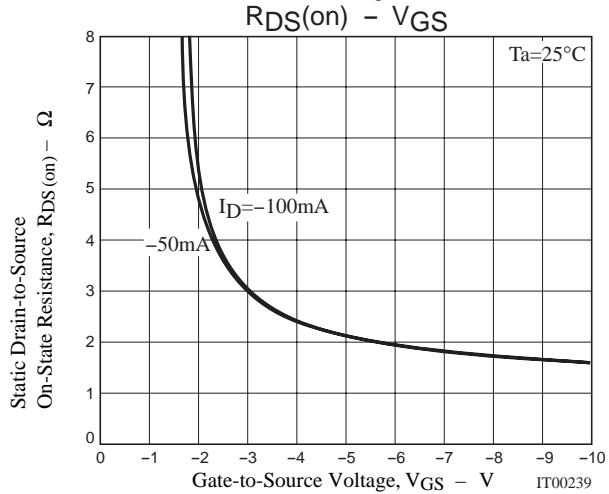
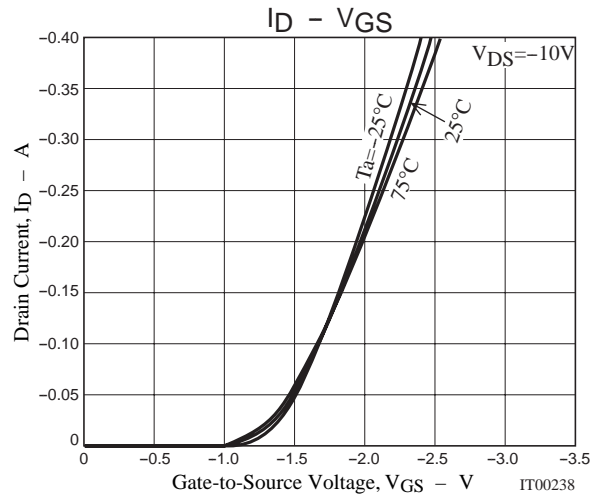
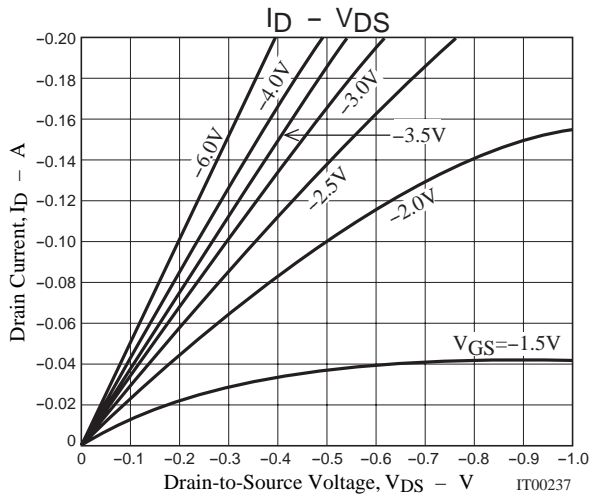
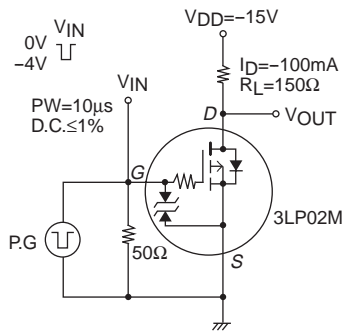
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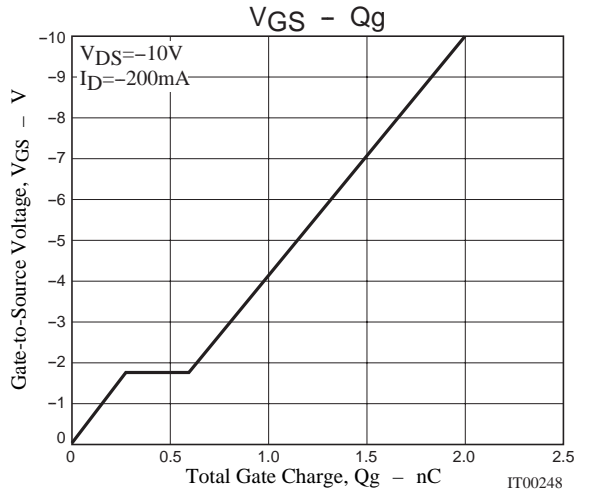
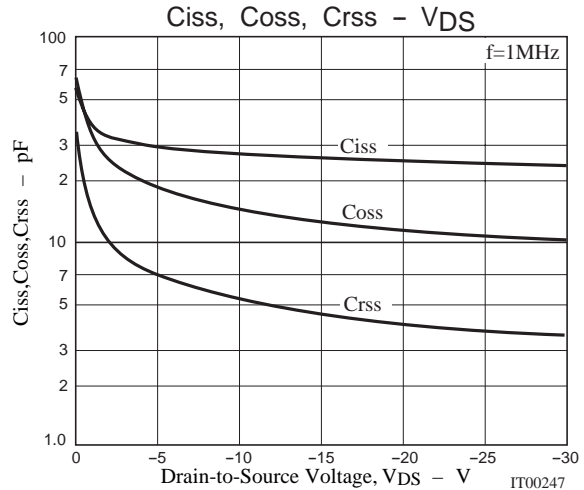
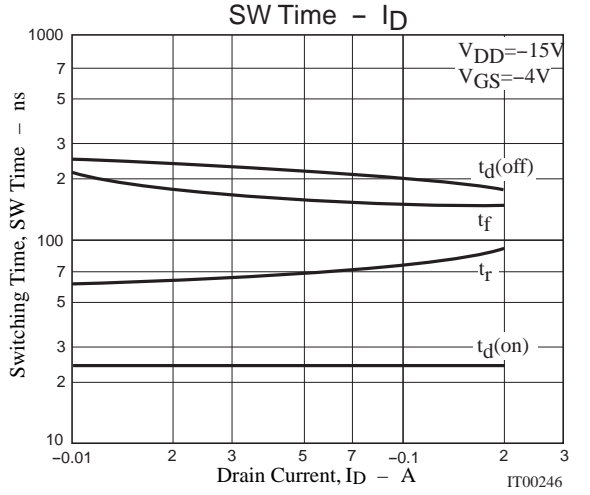
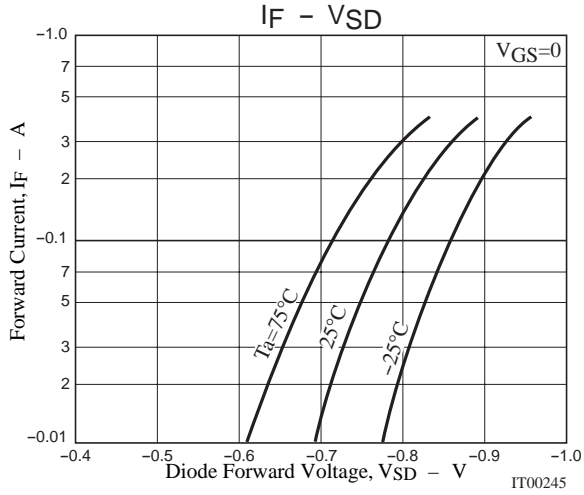
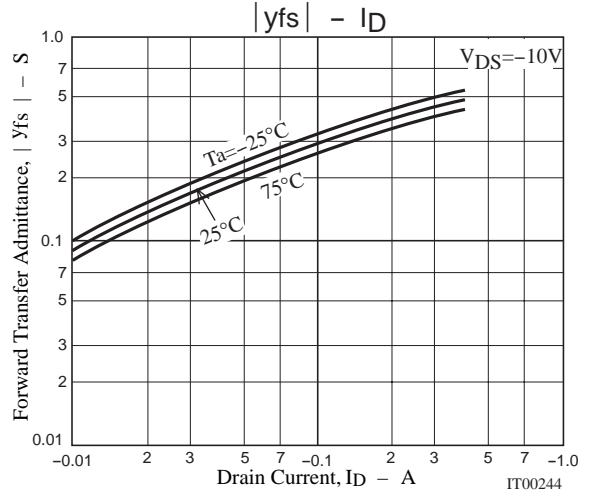
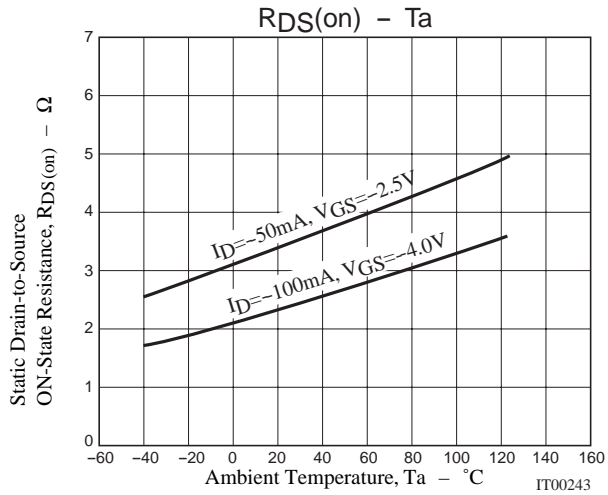
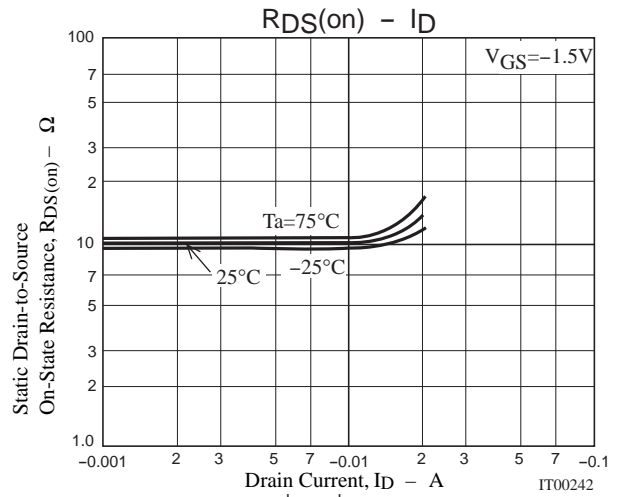
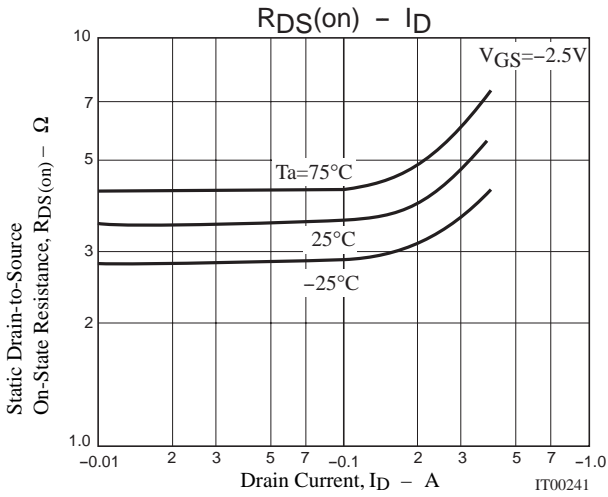
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	$C_{iss}$	$V_{DS}=-10V, f=1MHz$		28		pF
Output Capacitance	$C_{oss}$	$V_{DS}=-10V, f=1MHz$		15		pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS}=-10V, f=1MHz$		5.2		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit		24		ns
Rise Time	$t_r$	See specified Test Circuit		75		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit		200		ns
Fall Time	$t_f$	See specified Test Circuit		150		ns
Total Gate Charge	$Q_g$	$V_{DS}=-10V, V_{GS}=-10V, I_D=-200mA$		2		nC
Gate-to-Source Charge	$Q_{gs}$	$V_{DS}=-10V, V_{GS}=-10V, I_D=-200mA$		0.25		nC
Gate-to-Drain "Miller" Charge	$Q_{gd}$	$V_{DS}=-10V, V_{GS}=-10V, I_D=-200mA$		0.35		nC
Diode Forward Voltage	$V_{SD}$	$I_S=-200mA, V_{GS}=0$		-0.82	-1.2	V

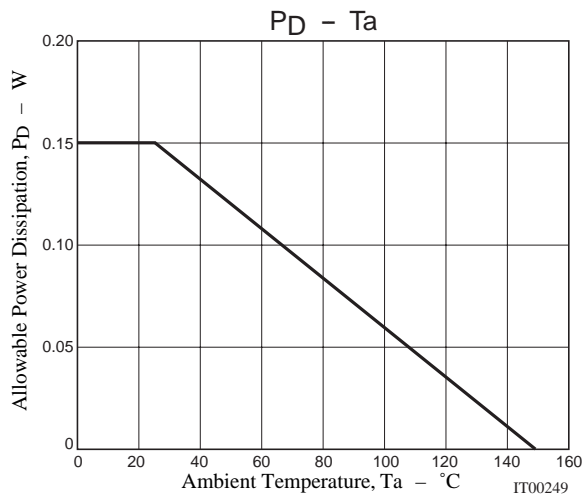
## Switching Time Test Circuit



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